

FORM PTO-1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO.: FIS920000227US2	Divisional Application of U.S. Serial No.: 09/885,790
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT: Divakaruni et al.	
(Use several sheets if necessary) (37 CFR 1.98(b))		FILING DATE:	PRIOR ART GROUP: 1765

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
PC	AA	5,895,253	04/20/1999	Akram			
PI	AB	5,998,251	12/07/1999	Wu et al.			
PI	AC	6,030,867	02/29/2000	Chien et al.			
PI	AD	6,265,302	07/24/2001	Lim et al.			
PI	AE	6,344,383	02/05/2002	Berry et al.			
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB- CLASS	TRANSLATION YES	NO
	AL							
	AM							
	AN							
	AO							
	AP							

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

PI	AQ	"A Novel Trench DRAM Cell with a <u>VERT</u> ical Access Transistor and <u>Buri</u> Ed <u>STrap</u> (VERI BEST) for 4Gb/16Gb", U. Gruening et al., IEDM 99-25, 1999.
PI	AR	"Extending Trench DRAM Technology to 0.15 μ m Groundrule and Beyond", T. Rupp et al., IEDM 99-33, 1999.
PI	AS	"A 0.135 μ m ² 6F ² Trench-Sidewall Vertical Device Cell for 4Gb/16Gb DRAM", C. J. Radens et al., 2000 Symposium on VLSI Technology Digest of Technical Papers, pp. 80-81, IEEE, 2000.
EXAMINER <i>[Signature]</i>		DATE CONSIDERED 08/02/00
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance <u>and</u> not considered. Include copy of this form with next communication to applicant.		